

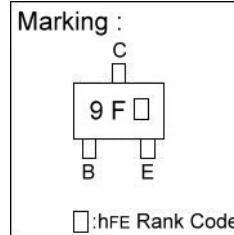
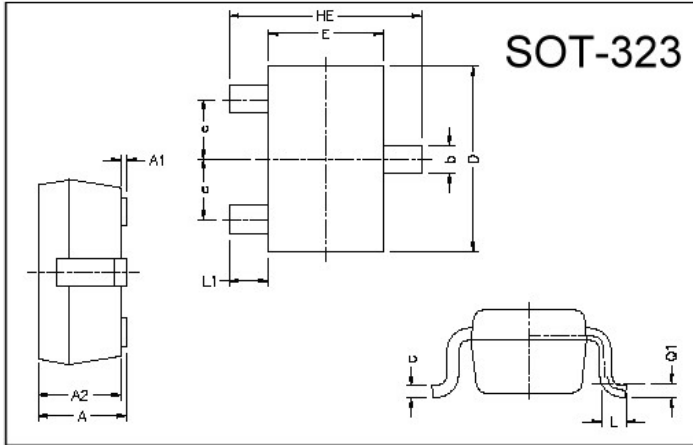
## GSBC807

### PNP EPITAXIAL PLANAR TRANSISTOR

#### Description

The GSBC807 is designed for switching and AF amplifier application, suitable for driver storages and low power output storages.

#### Package Dimensions



| REF. | Millimeter |      | REF. | Millimeter |      |
|------|------------|------|------|------------|------|
|      | Min.       | Max. |      | Min.       | Max. |
| A    | 0.80       | 1.10 | L1   | 0.42 REF.  |      |
| A1   | 0          | 0.10 | L    | 0.15       | 0.35 |
| A2   | 0.80       | 1.00 | b    | 0.25       | 0.40 |
| D    | 1.80       | 2.20 | c    | 0.10       | 0.25 |
| E    | 1.15       | 1.35 | e    | 0.65 REF.  |      |
| HE   | 1.80       | 2.40 | Q1   | 0.15 BSC.  |      |

#### Absolute Maximum Ratings at Ta = 25°C

| Parameter                    | Symbol | Ratings    | Unit |
|------------------------------|--------|------------|------|
| Junction Temperature         | Tj     | +150       | °C   |
| Storage Temperature          | Tstg   | -55 ~ +150 | °C   |
| Collector to Base Voltage    | VCBO   | -50        | V    |
| Collector to Emitter Voltage | VCEO   | -45        | V    |
| Emitter to Base Voltage      | VEBO   | -5         | V    |
| Collector Current            | IC     | 800        | mA   |
| Total Power Dissipation      | PD     | 225        | mW   |

#### Characteristics at Ta = 25°C

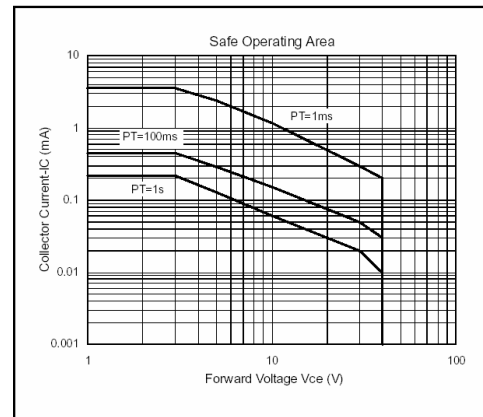
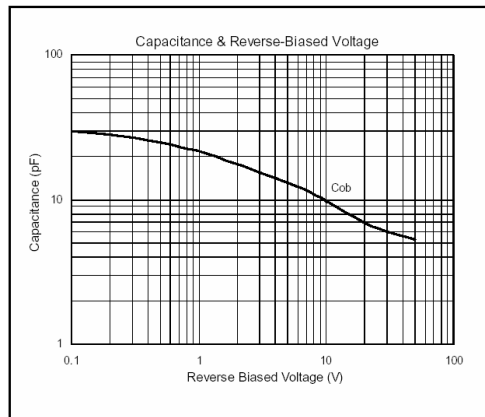
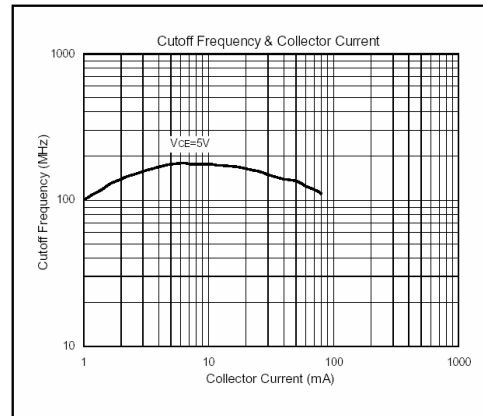
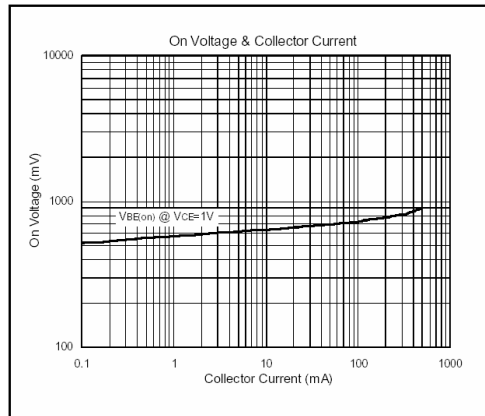
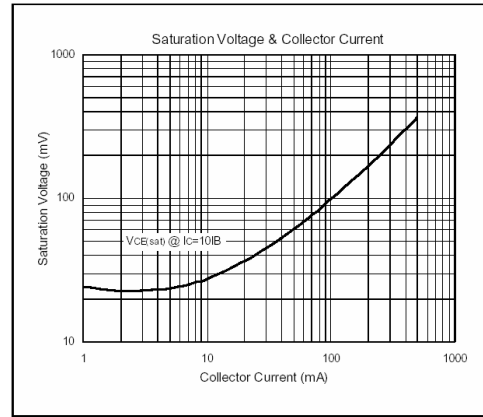
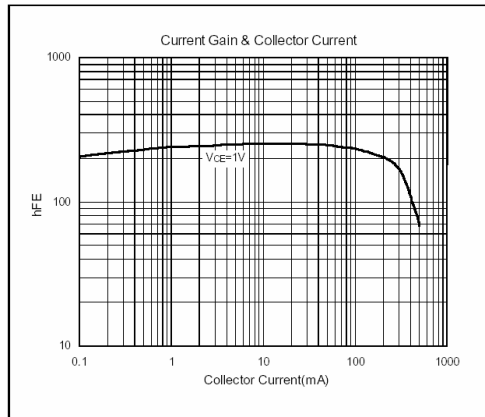
| Symbol    | Min. | Typ. | Max. | Unit | Test Conditions             |
|-----------|------|------|------|------|-----------------------------|
| BVGB0     | -50  | -    | -    | V    | IC=-100uA                   |
| BVGEO     | -45  | -    | -    | V    | IC=-10mA                    |
| BVCES     | -50  | -    | -    | V    | IC=-100uA                   |
| BVEBO     | -5   | -    | -    | V    | IE=-100uA                   |
| ICES      | -    | -    | -100 | nA   | VCE=-25V                    |
| IEBO      | -    | -    | -100 | nA   | VEB=-4V                     |
| *VCE(sat) | -    | -    | -700 | mV   | IC=500mA, IB=50mA           |
| *VBE(on)  | -    | -    | -1.2 | V    | VCE=-1V, IC=300mA           |
| *hFE      | 100  | -    | 630  |      | VCE=-1V, IC=100mA           |
| fT        | -    | 100  | -    | MHz  | VCE=-5V, IC=-10mA, f=100MHz |
| Cob       | -    | -    | 12   | pF   | VCB=-10V, f=1MHz, IE=0A     |

\* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

#### Classification Of hFE

| Rank  | 9FA       | 9FB       | 9FC       |
|-------|-----------|-----------|-----------|
| Range | 100 - 250 | 160 - 400 | 250 - 630 |

## Characteristics Curve



### Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

### Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.  
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China  
TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165